

Practitioner's Docket No.: TSL-125

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Yakov Roizin
 Assignee: Tower Semiconductor Ltd.
 Serial No.: 10/659,031
 Filed: 9/9/2003
 For: "Protection Against In-Process Charging In Silicon-Oxide-Nitride-Oxide-Silicon (SONOS) Memories"

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Mail Stop Amendment
 Commissioner for Patents
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RESPONSE TO RESTRICTION REQUIREMENT

Sir:

In response to the outstanding Office Action dated October 28, 2004, in which the Examiner imposed a restriction requirement to election of invention for the above-referenced application, Applicant elects to prosecute the invention as in Species I, Claims 1-13 and 22-29 drawn to a pre-metal dielectric structure for a silicon-nitride-oxide-silicon (SONOS) memory transistor and manufacturing method, without traverse.

Applicant reserves the right to file divisional applications on the non-elected claims.

Respectfully submitted,



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CERTIFICATE OF TRANSMISSION (37 C.F.R. 1.8(a))

I hereby certify that, on the date shown below, this correspondence is being transmitted by facsimile to the Patent and Trademark Office.

Date: 11/23/04 Signature: Carrie Reddick
 Resent 11/26/04 Signature: Carrie Reddick